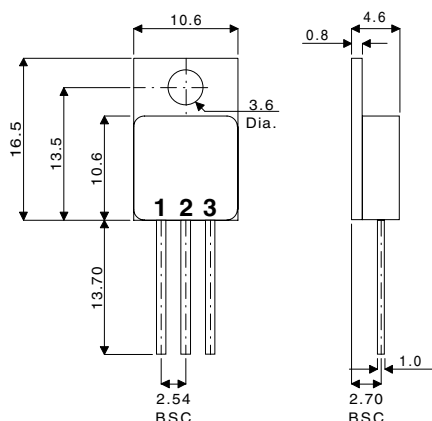
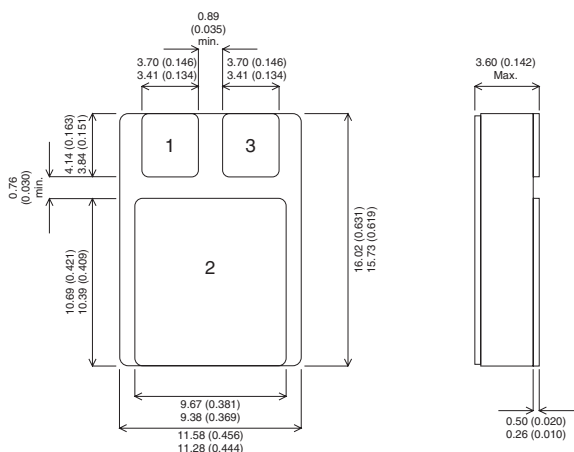


MECHANICAL DATA (Dimensions in mm)



TO220M (TO257AB) Metal Package - Isolated
Pin 1 – Base Pin 2 – Collector Pin 3 – Emitter



SMD1 (TO276AB) Ceramic Surface Mount Package
Pad 1 – Base Pad 2 – Collector Pad 3 – Emitter

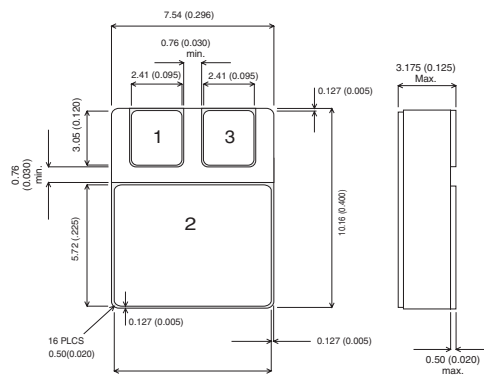
SILICON PNP EPITAXIAL BASE IN TO220 METAL AND SMD CERAMIC SURFACE MOUNT PACKAGES

FEATURES

- HERMETIC METAL OR CERAMIC PACKAGES
- HIGH RELIABILITY
- MILITARY AND SPACE OPTIONS
- SCREENING TO CECC LEVELS
- FULLY ISOLATED (METAL VERSION)

APPLICATIONS

- POWER LINEAR AND SWITCHING APPLICATIONS
- GENERAL PURPOSE POWER



SMD05 (TO276AA) Ceramic Surface Mount Package
Pad 1 – Base Pad 2 – Collector Pad 3 – Emitter

ABSOLUTE MAXIMUM RATINGS ($T_{case}=25^{\circ}C$ unless otherwise stated)

		BDS18	BDS19
V_{CBO}	Collector - Base voltage ($I_E = 0$)	-120V	-150V
V_{CEO}	Collector - Emitter voltage ($I_B = 0$)	-120V	-150V
V_{EBO}	Emitter - Base voltage ($I_C = 0$)	-5V	-150V
I_E, I_C	Emitter, Collector current	-8A	-150V
I_B	Base current	-2A	-150V
P_{tot}	Total power dissipation at $T_{case} = 25^{\circ}C$	43.75W	-150V
T_{stg}	Storage Temperature	-65 TO 200°C	-150V
T_j	Junction Temperature	200°C	-150V

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO} Collector cut-off current ($I_E = 0$)	BDS18 $V_{CB} = -120V$ BDS19 $V_{CB} = -150V$			-20 -20	μA
I_{CEO} Collector cut-off current ($I_B = 0$)	BDS18 $V_{CE} = -60V$ BDS19 $V_{CE} = -75V$			-0.1 -0.1	mA
I_{EBO} Emitter cut-off current ($I_C = 0$)	$V_{EB} = -5V$			-10	μA
$V_{(BR)CEO}^*$ Collector - Emitter Breakdown Voltage	BDS18 $I_B = 0$ BDS19 $I_C = -10mA$	-120 -150			V
$V_{CE(sat)}^*$ Collector - Emitter saturation voltage	$I_C = -0.5A$ $I_B = -0.05A$ $I_C = -4.0A$ $I_B = -0.4A$			-0.4 -1.5	V V
$V_{BE(on)}^*$ Base - Emitter voltage	$V_{CE} = -2V$ $I_C = -1.0A$			-1.0	V
h_{FE}^* DC Current gain	$I_C = -0.5A$ $V_{CE} = -2V$ $I_C = -4A$ $V_{CE} = -2V$	40 15		250 150	
f_T Transition frequency	$I_C = -0.5A$ $V_{CE} = -4V$ $F = 20MHz$	30			MHz

*Pulsed : Pulse duration = 300 μs , duty cycle = 1.5%

SWITCHING CHARACTERISTICS

Parameter	Test Conditions	Max.	Unit
t_{on} On Time ($t_d + t_r$)	$I_C = -2A$ $V_{CC} = -80V$ $I_{B1} = 0.2A$	0.5	μs
t_s Storage Time		1.5	
t_f Fall Time		0.3	

THERMAL DATA

$R_{THj-case}$	Thermal resistance junction to case	Max. 4.0 $^{\circ}C/W$
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